TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK2162

AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

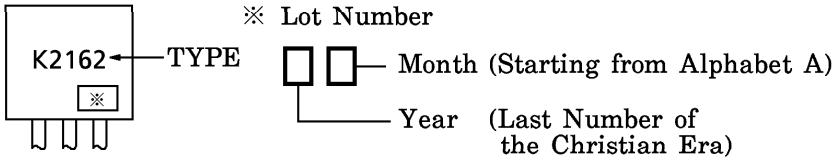
INDUSTRIAL APPLICATIONS

- High Breakdown Voltage : V_{DSS} = 180 V
- High Forward Transfer Admittance : $|Y_{fs}|$ = 0.7 S (Typ.)
- Complementary to 2SJ338

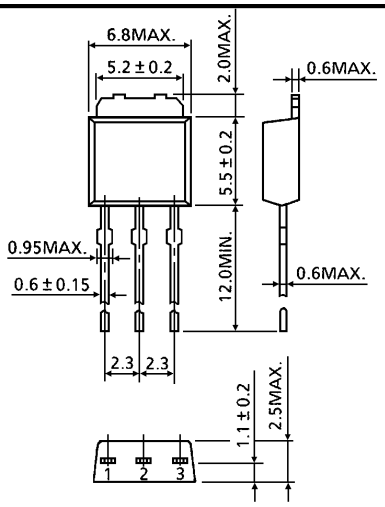
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	180	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current	I_D	1	A
Power Dissipation (Tc = 25°C)	P_D	20	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

MARKING



Unit in mm



1. GATE
2. DRAIN (HEAT SINK)
3. SOURCE

JEDEC	—
EIAJ	SC-64
TOSHIBA	2-7B1B

Weight : 0.36 g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	V_{DS} = 0, V_{GS} = ±20 V	—	—	±100	nA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 10 mA, V_{GS} = 0 V	180	—	—	V
Gate -Source Cut-off Current	$V_{GS(OFF)}$	V_{DS} = 10 V, I_D = 10 mA	1.4	—	2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	I_D = 0.6 A, V_{GS} = 10 V	—	1.7	3.0	V
Forward Transfer Admittance	$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 0.3 A	—	0.7	—	S
Input Capacitance	C_{iss}	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz	—	170	—	pF
Output Capacitance	C_{oss}		—	45	—	
Reverse Transfer Capacitance	C_{rss}		—	17	—	

This transistor is the electrostatic sensitive device.
Plese handle with caution.

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